JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

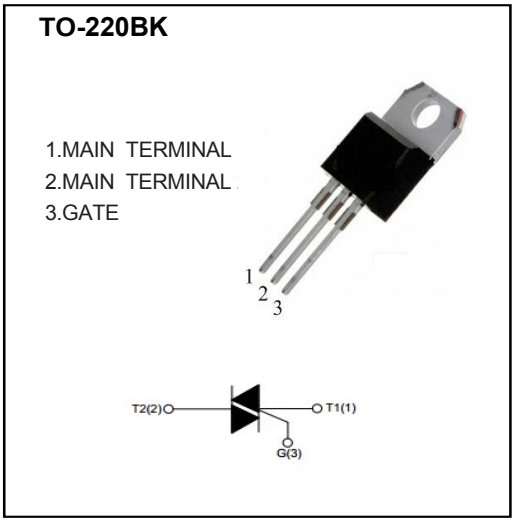
TO-220BK Plastic-Encapsulate Thyristors

CT304B 3Q TRIACs

MAIN CHARACTERISTICS

$I_{T(RMS)}$		4A
V_{DRM}/V_{RRM}	CT304B-600T/S	600V
	CT304B-800T/S	800V
V_{TM}		1.55V

TO-220BK



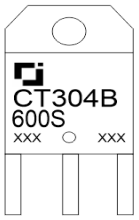
FEATURES

- NPNPN 5-layer Structure TRIACs
- Mesa Glass Passivated Technology
- Multi Layers Metal Electrodes
- High Junction Temperature
- Good Commutation Performance
- High dV/dt and dI/dt

APPLICATIONS

- Heater Control
- Motor Speed Controller
- Mixer

MARKING



CT304B:Series Code

600S:Depends on V_{DRM} and I_{GT}

XXX:Internal Code

ABSOLUTE RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Test condition		Value		Unit
V_{DRM}/ V_{RRM}	Repetitive peak off-state voltage	T_j=25℃	CT304B-600T/S	600		V
			CT304B-800T/S	800		V
$I_{T(RMS)}$	RMS on-state current	TO-220BK(T_C≤110℃), Fig. 1,2		4		A
I_{TSM}	Non repetitive surge peak on-state current	Full sine wave, T_j(init)=25℃, tp=20ms; Fig. 3,5		40		A
I^2t	I^2t value	tp=10ms		8		A^2s
dI_T/dt	Critical rate of rise of on-state current	I_G=2*I_{GT}, tr≤10ns, F=120Hz, T_j=125℃		Ⅰ-Ⅱ-Ⅲ	50	A/μs
				Ⅳ	n/a	
I_{GM}	Peak gate current	tp=20μs, T_j=125℃		4		A
$P_{G(AV)}$	Average gate power	T_j=125℃		1		W
T_{STG}	Storage temperature			-40~+150		℃
T_j	Operating junction temperature			-40~+125		

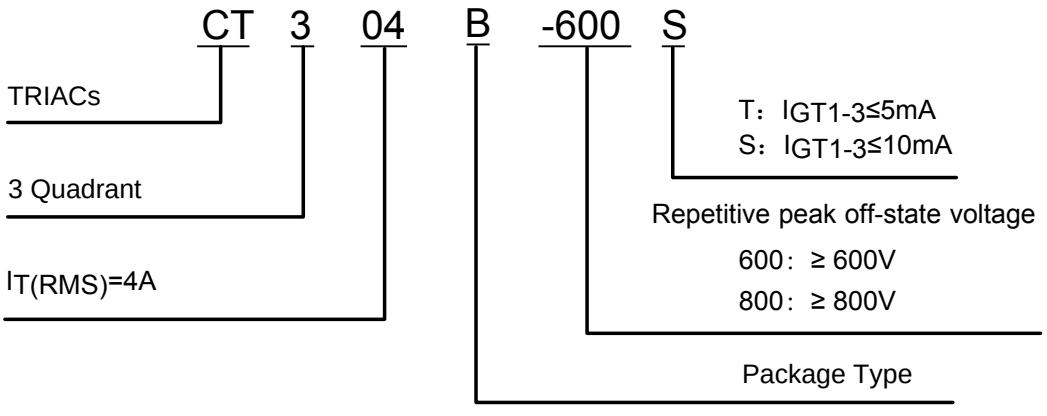
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Symbol	Parameter	Test condition		Value		Unit
				T	S	
I_{GT}	Gate trigger current	V_D=12V, R_L=30 Ω T_j=25℃, Fig. 6	Ⅰ-Ⅱ-Ⅲ	≤5	≤10	mA
			Ⅳ	n/a	n/a	
V_{GT}	Gate trigger voltage		Ⅰ-Ⅱ-Ⅲ	≤1.3		V
V_{GD}	Non-triggering gate voltage	VD=VDRM, T_j=125℃		≥0.2		V
I_H	Holding current	I_T=100mA, Fig. 6		≤10	≤15	mA
I_L	Latching current	I_G=1.2I_{GT} Fig. 6	Ⅰ-Ⅲ	≤10	≤25	mA
			Ⅱ	≤15	≤30	mA
dV_D/dt	Critical rate of rise of off-state	V_D=67%V_{DRM}, Gate Open T_j=125℃		≥20	≥40	V/μs
V_{TM}	On-state Voltage	I_{TM}=8.5A，tp=380μs, Fig. 4		≤1.55		V
I_{DRM} / I_{RRM}	Repetitive peak off-state current	V_D=V_{DRM}/V_{RRM}, T_j=25℃		≤5	≤5	μA
		V_D=V_{DRM}/V_{RRM}, T_j=125℃		≤1	≤1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-c)	Junction to case (AC)	TO-220BK	2.6	℃/W
Rth (j-a)	Junction to ambient	TO-220BK	60	℃/W

PART NUMBER



CHARACTERISTICS CURVES

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

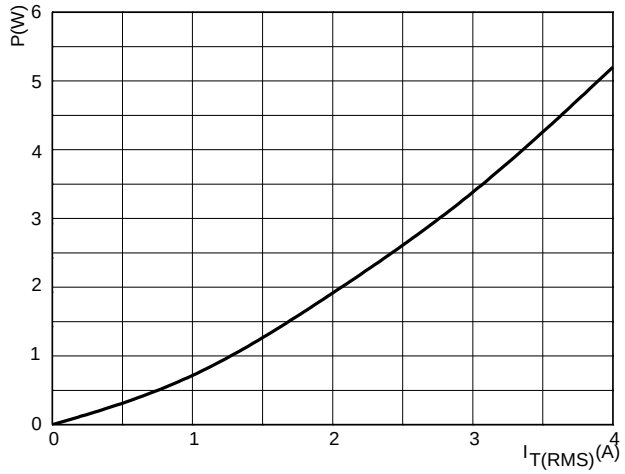


FIG.2: RMS on-state current versus case temperature (full cycle)

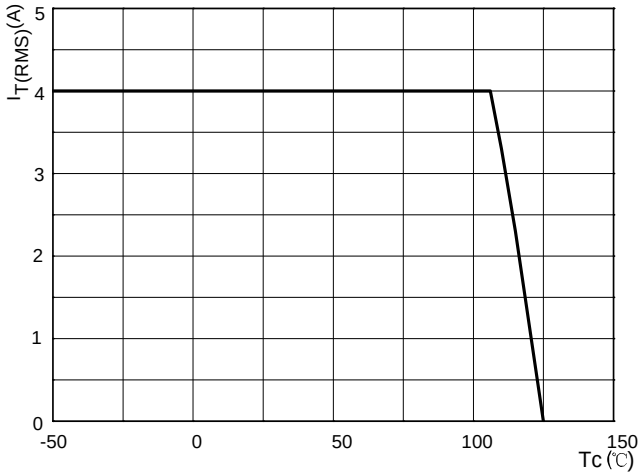


FIG.3: Surge peak on-state current versus number of cycles

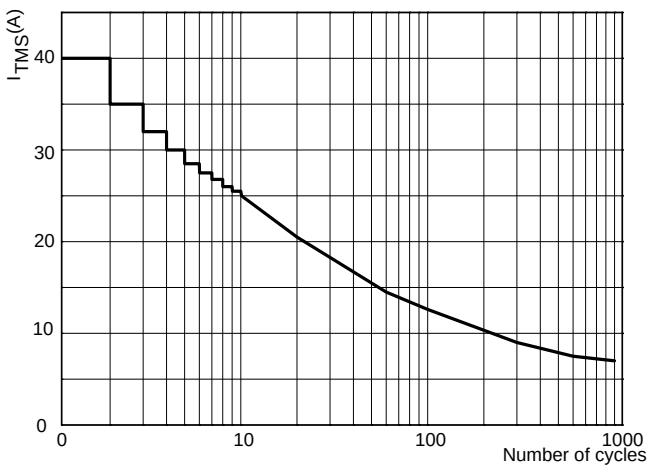


FIG.4: On-state characteristics (maximum values)

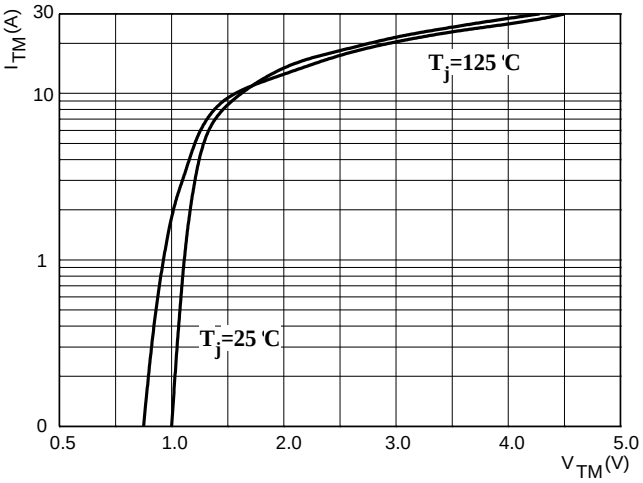


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms

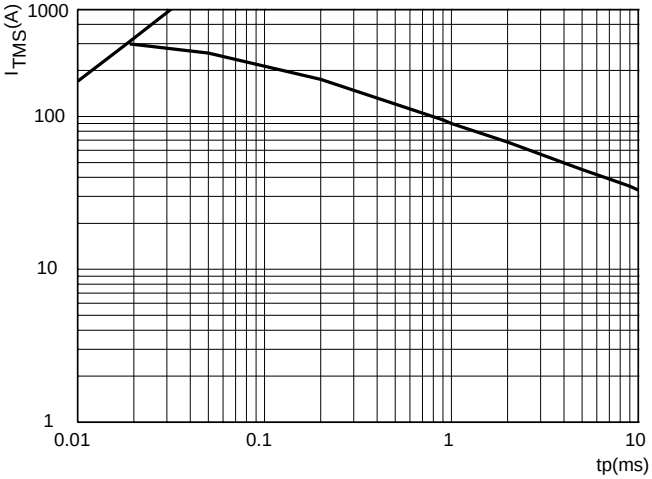
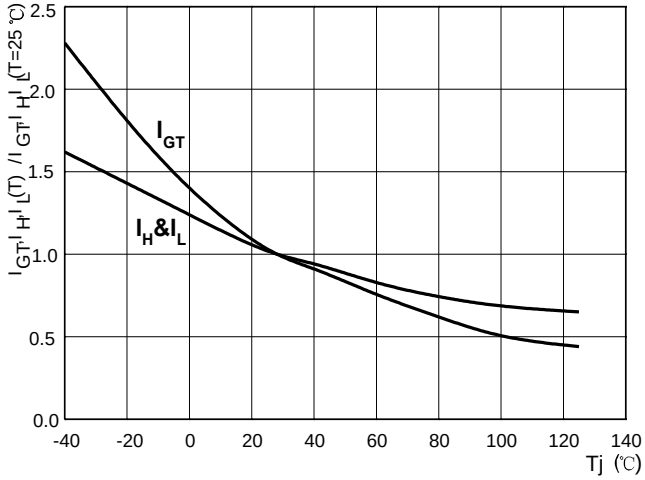
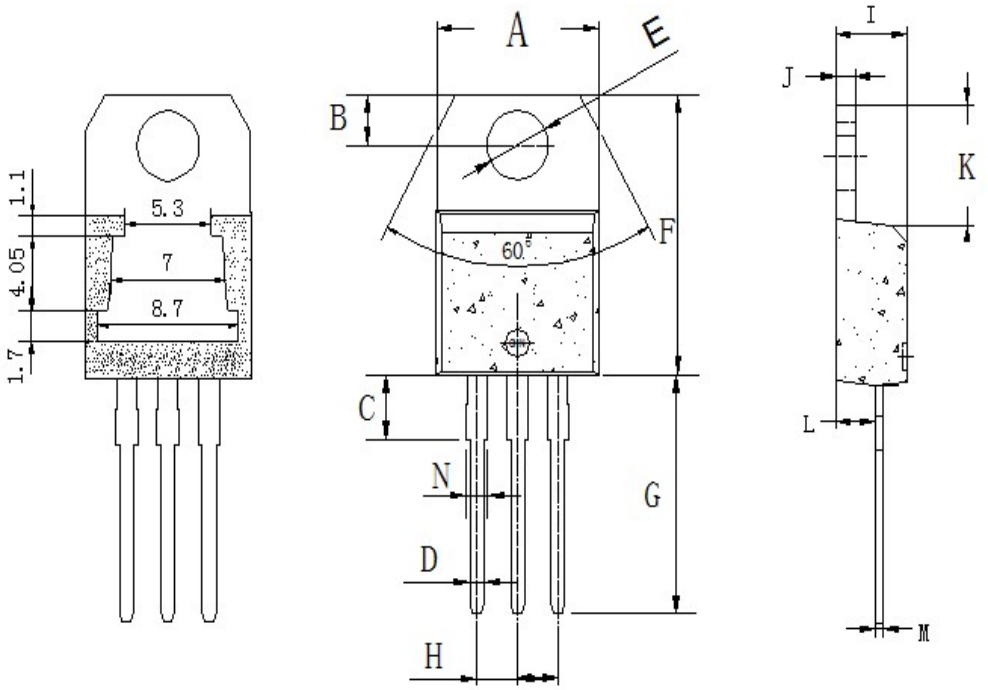


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



TO-220BK PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	9.8	10.4	0.385	0.409
B	2.65	3.1	0.104	0.122
C	2.8	4.2	0.110	0.165
D	0.7	0.92	0.027	0.036
E	3.75	3.95	0.147	0.155
F	14.8	16.1	0.582	0.633
G	13.05	13.6	0.513	0.535
H	2.4	2.7	0.094	0.106
I	4.38	4.61	0.172	0.181
J	1.15	1.36	0.045	0.053
K	5.85	6.82	0.230	0.268
L	2.35	2.75	0.092	0.108
M	0.35	0.65	0.013	0.025
N	1.18	1.42	0.046	0.055